

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

### R-C THERMAL MODEL FOR TANK CONFIGURATION

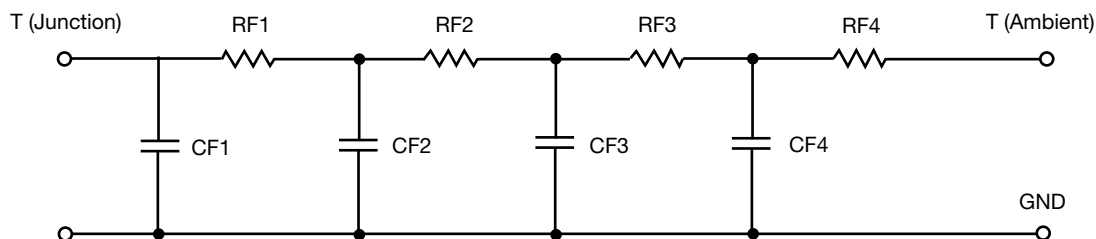


R-C VALUES FOR TANK CONFIGURATION			
THERMAL RESISTANCE (°C/W)			
Junction to	Ambient	Case	Foot
RT1	N/A	861.5801m	N/A
RT2	N/A	1.2210	N/A
RT3	N/A	281.2678m	N/A
RT4	N/A	637.9607m	N/A
THERMAL CAPACITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	N/A	200.7271m	N/A
CT2	N/A	29.7576m	N/A
CT3	N/A	1.3564m	N/A
CT4	N/A	9.0116m	N/A

#### Note

N/A indicates not applicable

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION**

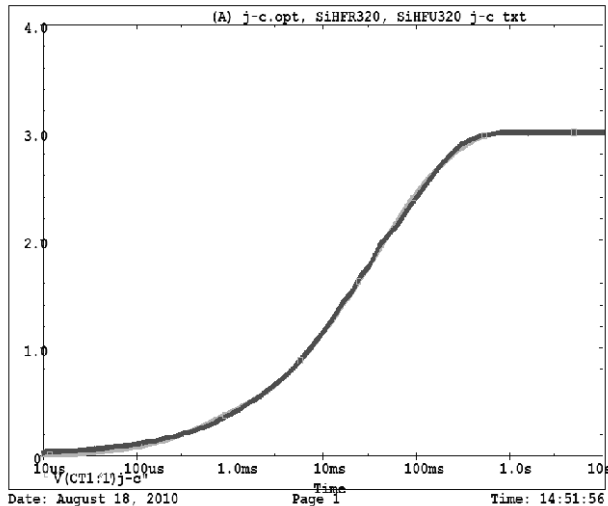
<b>R-C VALUES FOR FILTER CONFIGURATION</b>			
<b>THERMAL RESISTANCE (°C/W)</b>			
<b>Junction to</b>	<b>Ambient</b>	<b>Case</b>	<b>Foot</b>
RF1	N/A	355.5050m	N/A
RF2	N/A	1.1735	N/A
RF3	N/A	1.2516	N/A
RF4	N/A	218.5629m	N/A
<b>THERMAL CAPACITANCE (Joules/°C)</b>			
<b>Junction to</b>	<b>Ambient</b>	<b>Case</b>	<b>Foot</b>
CF1	N/A	979.1563u	N/A
CF2	N/A	6.0451m	N/A
CF3	N/A	45.4738m	N/A
CF4	N/A	805.0117m	N/A

**Note**

N/A indicates not applicable



SiHFR320, SiHFU320 Tank j-c Temperature: 27.0



SiHFR320, SiHFU320 Filter j-c Temperature: 27.0

